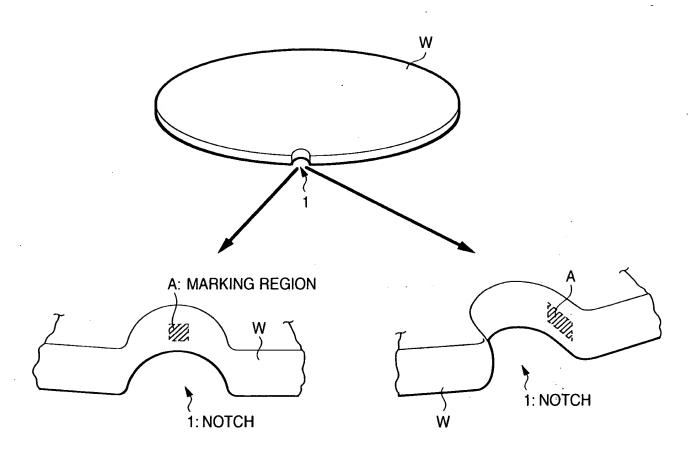
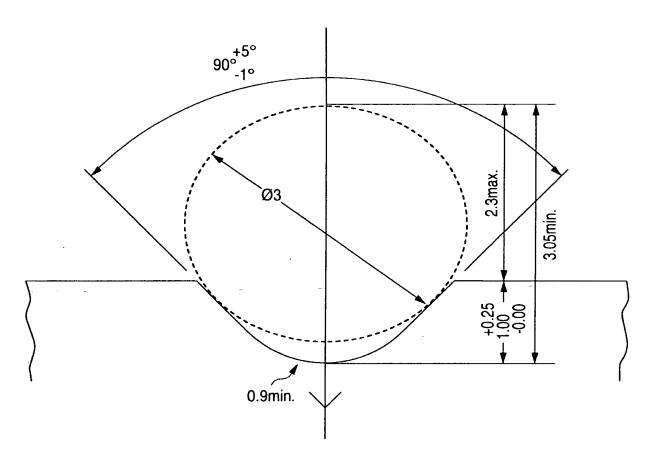
FIG. 1



EXPLANATORY VIEW SHOWING A SEMICONDUCTOR WAFER ACCORDING TO THE INVENTION IN WHICH MARKING IS CARRIED OUT ON A PORTION OF A NOTCH PORTION

FIG. 2



PLANE VIEW SHOWING A RELATIONSHIP BETWEEN A SHAPE OF A NOTCH AND A PIN INSERTED INTO THE NOTCH

FIG. 3A

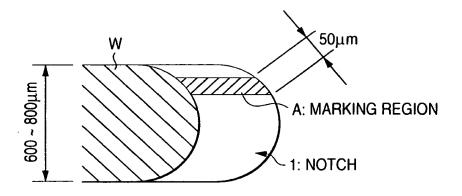


FIG. 3B

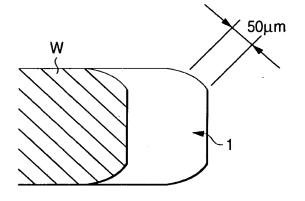
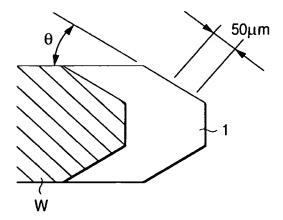


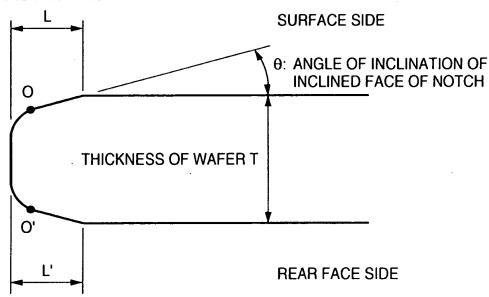
FIG. 3C



SECTIONAL VIEWS SHOWING EXAMPLES OF SECTIONAL SHAPES OF A PERIPHERAL EDGE PORTION OF A SEMICONDUCTOR WAFER

FIG. 4

HORIZONTAL DIMENSION OF INCLINED FACE



SECTIONAL VIEW SHOWING A SECTIONAL FACE OF A PERIPHERAL EDGE PORTION ACCORDING TO AN EMBODIMENT OF THE INVENTION

FIG. 5

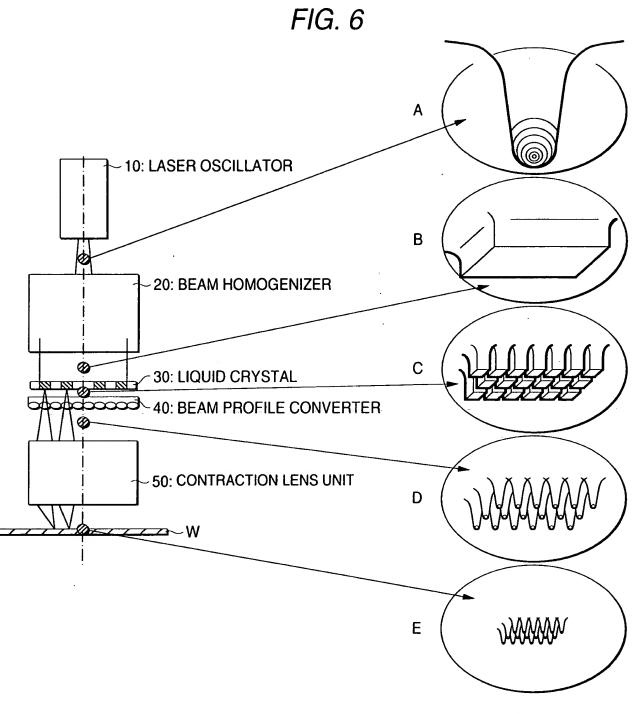
50µm

1µm

600µm

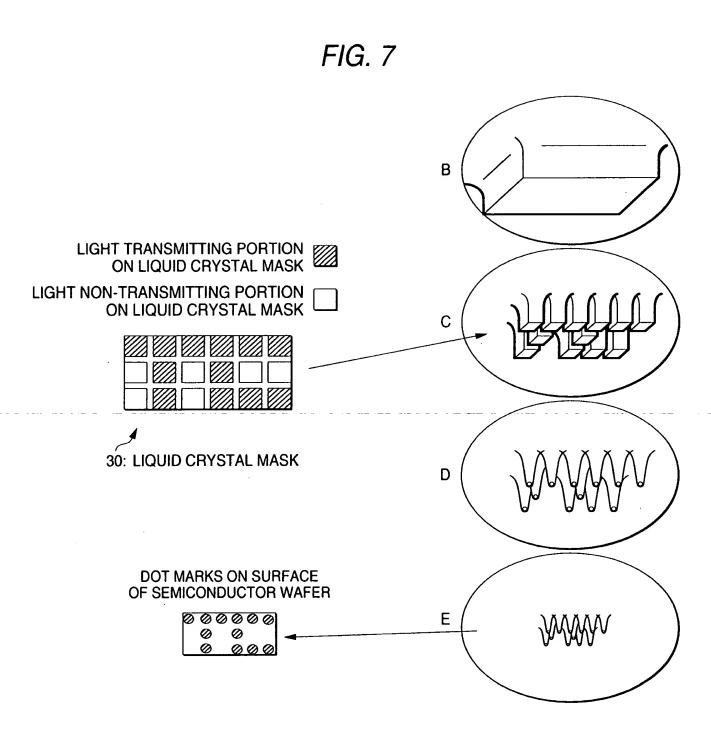
1: NОТСН

PLANE VIEW SHOWING A DIFFERENCE IN A DIMENSION OF A WALL FACE IN A MARKING REGION OF AN INNER WALL FACE OF A NOTCH



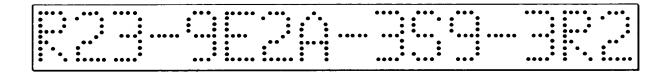
[ENERGY DENSITY DISTRIBUTION OF LASER BEAM]

EXPLANATORY VIEW SCHEMATICALLY SHOWING A VERY SMALL DOT MARKING APPARATUS APPLIED TO THE INVENTION AND A PROCEDURE OF CONVERTING AN ENERGY DENSITY DISTRIBUTION (BEAM PROFILE) OF LASER BEAM



EXPLANATORY VIEW SCHEMATICALLY SHOWING DOT MARKS FORMED IN ACCORDANCE WITH A DISPLAY PATTERN OF A LIQUID CRYSTAL MASK IN A MARKING APPARATUS AND A PROCEDURE OF CONVERTING AN ENERGY DISTRIBUTION OF LASER BEAM





PLANE VIEW SHOWING ALPHANUMERIC CHARACTERS BY DOT MARKS INSCRIBED ON AN INCLINED FACE OF A NOTCH OF A SEMICONDUCTOR WAFEB